Page 1 of 1 SERIAL NO. U.S. DEPARTMENT OF COMMERCE ATTY, DOCKET NO. Form PTO-1449 PATENT AND TRADEMARK OFFICE 039153-0441 (GO406) 10/017,855 (MODIFIED) APPLICANT Philip A. Fisher et al. INFORMATION DISCLOSURE CIT ILING DATE **GROUP ART UNIT** (Use several sheets if necessary) SEP 1 1 7003 2823 12/14/2001 AU.S. PATENT DOCUMENTS FILING DATE SUB-DOCUMENT **EXAMINER** NAME **CLASS** DATE REF **CLASS** INITIAL NUMBER **APPROPRIATE** 05/02/2000 07/16/2002 Pike et al. 436 313 6.420,097 Α1 07/27/2500 05/28/2002 Ishii et al. 6.395,447 430 191 A2 12/28/1999 03/19/2002 Wong et al. 6,358,670 296 430 A3 Wong et al. 01/11/1999 11/20/2001 6.319.655 430 311 A4 08/20/1999 765 03/13/2001 Oh et al. 6,200,903 A5 438 01/16/2001 Tao et al. 11/19/1999 733 6,174,818 438 A6 05/02/2000 Hanawa 6,057,066 09/16/199c 430 A7 Liu et al. 10/18/1996 5,994,225 11/30/1999 694 438 **A8** 10/05/1999 Yen et al. 09/10/1997 , 5,962,195 A9 436 316 08/19/1997 12/11/1995 ,15,658,469 Jennison 478 A10 611 liv 06/21/1982 1 4,446,222 05/01/1984 Kress 430 307 A11 438 09/08/1982 4,394,211 07/19/1983 Uchiyama et al. 623 A12 FOREIGN PATENT DOCUMENTS TRANSLATION SUB-DOCUMENT DATE COUNTRY CLASS REF **CLASS** NUMBER YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Patent Abstracts of Japan for Japanese Patent Application No. 09252189, 9 April 1999 (1 pg.). A13 Chiong et al., "Resist contrast enhancement in high resolution electron beam lithography," Journal of Vacuum Science & Technology, Volume 7, No. 6, November 1989, pgs. 1771-1777 (8 pgs.). A14 Lee et al., "Fabrication of 0.06 µm Poly-Si Gate Using DUV Lithography with a Designed Six Oy Nz Film as an Arc and Hardmask, Symposium on VLSI Technology Digest of Technical Papers, 1997, pps. 131-132 (2 pgs.). A15 \mathcal{D} D. W. Hess and D. B. Graves, "Plasma-Enhanced Etching and Deposition," Microelectronics Processing, (Eds.: D. W. Hess & K. F. Jensen) ACS (1989), Ch. 8 pp. 337-440 (34 pgs.). A16 Yang et al., "Electronic Beam Processing for Spin-on Polymers and its Applications to Back-End-of-Line (BEOL) Integration, Materials Research Society Symposium Proceedings. Vol. 511, April 1998 (7 pgs.). A17 PCT International Search Report for PCT/US02/05640 dated 10/02/2002 (7 pgs.). we A18 International Preliminary Examination Report for PCT/US02/05640 dated 07/03/2003 (8 pgs.). illi A19 **DATE CONSIDERED** EXAMINER 18 05 3003 lin (Maldusal EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include any copy of this form with next communication to applicant.